

MITSUBISHI LASER DIODES
ML7XX4 SERIES

InGaAsP—MQW—DFB LASER DIODES

TYPE
NAME

ML7924

DESCRIPTION

ML7XX4 series are MQW*—DFB** laser diodes emitting light beam around 1310nm.

They are well suited for light source in longdistance analog transmission system for example cable television (CATV).The ML7924 are specially designed for fiber modules and mount on flat open packages.

Rear output can be used for automatic power control of the laser.

*MQW : Multiple Quantum Well

**DFB : Distributed Feedback

FEATURES

- Excellent low distortion characteristic
CSO typical-60dBc/CTB typical-65dBc
under NTSC 78-channel transmission test
 - Modulation depth $m = 3.5\%$ /channel
 - $P_o = 10\text{mW}$ to 25mW
 - 20km single mode fiber
- Low relative intensity noise characteristic
(typical - 155dB/Hz)
- Low threshold current (typical 10mA)
- High-side mode suppression ratio (typical 40dB)

APPLICATION

Long-distance analog transmission system, especially for optical CATV

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Conditions	Ratings	Unit
P _o	Light output power	CW	30	mW
V _{RL}	Reverse voltage (Laser diode)	—	2	V
T _c	Case temperature	—	+20~+30	°C
T _{stg}	Storage temperature	—	-40~+100	°C

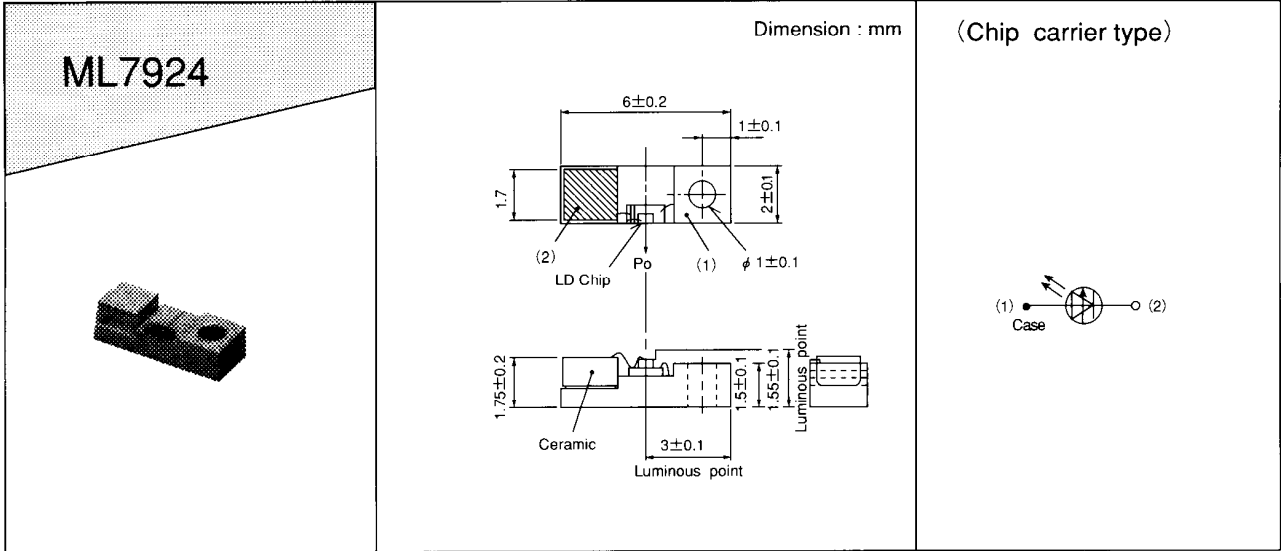
ELECTRICAL/OPTICAL CHARACTERISTICS (T_c = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I _{th}	Threshold current	CW	—	10	20	mA
I _{OP}	Operating current	CW, P _o = 10mW	—	35	60	mA
V _{OP}	Operating voltage	CW, P _o = 10mW	—	1.2	1.8	V
η	Slope efficiency	CW, P _o = 10mW	0.25	0.4	—	mW/mA
λ_P	Peak wavelength	CW, P _o = 10mW	1290	1310	1330	nm
θ_{\parallel}	Beam divergence angle (parallel)	CW, P _o = 10mW	—	25	35	deg.
θ_{\perp}	Beam divergence angle (perpendicular)	CW, P _o = 10mW	—	30	40	deg.
SMSR	Side mode suppression ratio	CW, P _o = 10mW	30	40	—	dB
P _m	Monitoring output	CW, P _o = 10mW	—	0.5	—	mW
CSO	Composite second order	78-channel transmission test, modulation depth $m = 3.5\%$ /channel, P _o (average) = 10 to 25mW 20Km single mode fiber	—	-60	—	dBc
CTB	Composite triple beat		—	-65	—	dBc
CNR	Carrier to noise ratio		—	52	—	dB
RIN	Relative intensity noise		CW, P _o = 10mW to 25mW, measuring frequency $f_m = 550\text{MHz}$	—	-155	—

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OUTLINE DRAWINGS



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TYPICAL CHARACTERISTICS

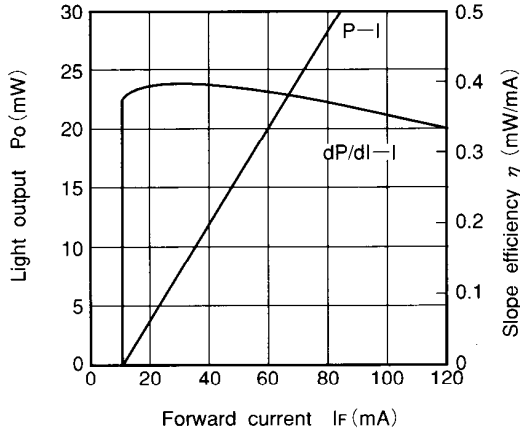


Fig.1 Light output vs. forward current

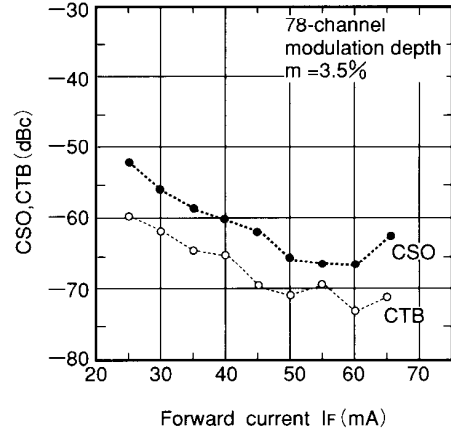


Fig.2 CSO/CTB vs. forward current

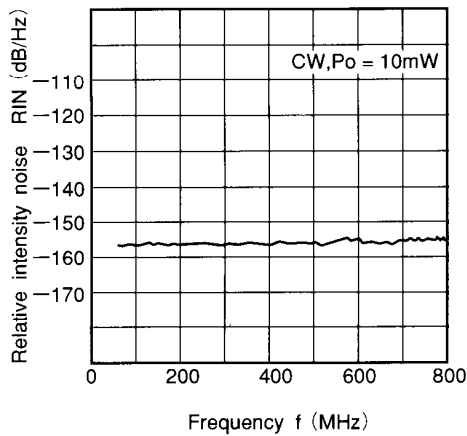


Fig.3 Relative intensity noise vs. frequency

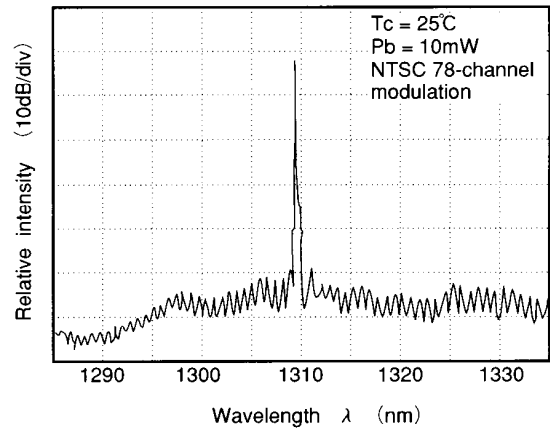


Fig.4 Spectrum under modulated operation

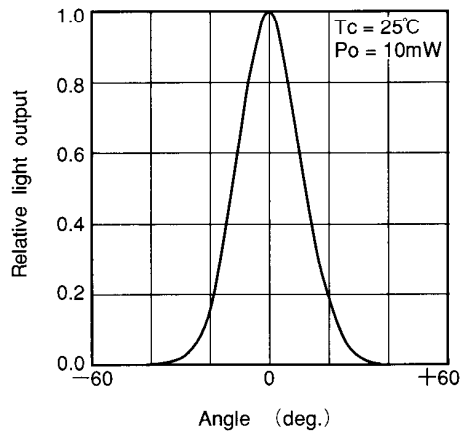


Fig.5-1 Far field pattern θ_{\parallel}

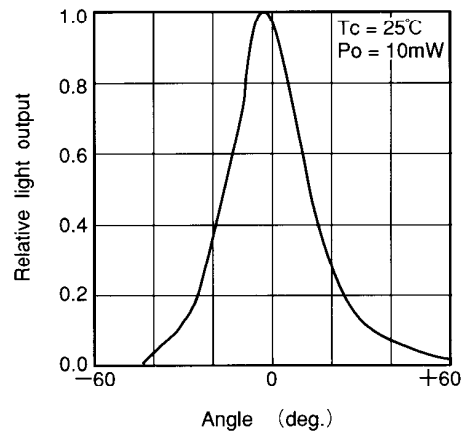


Fig.5-2 Far field pattern θ_{\perp}